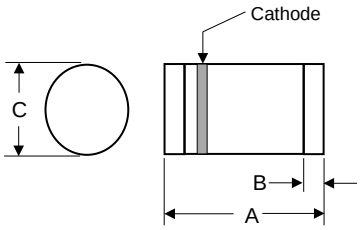
BAV101 THRU BAV103

Silicon Epitaxial Planar Diodes

Features

* High Voltage Switching Diodes

RoHS COMPLIANT



LL-34				
DIM	INCHES		MM	
	MIN	MAX	MIN	MAX
A	0.134	0.142	3.40	3.60
B	0.008	0.016	0.20	0.40
C	0.055	0.059	1.40	1.50

Maximum Ratings (TA=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage BAV101 BAV102 BAV103	V_{RRM}	 120 200 250	V
Reverse Voltage BAV101 BAV102 BAV103	V_R	 100 150 200	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current at t = 1 s at t = 100 μs at t = 1 μs	I_{FSM}	 1 3 9	A
Total Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	175	℃
Storage Temperature Range	T_{stg}	- 65 to + 175	℃

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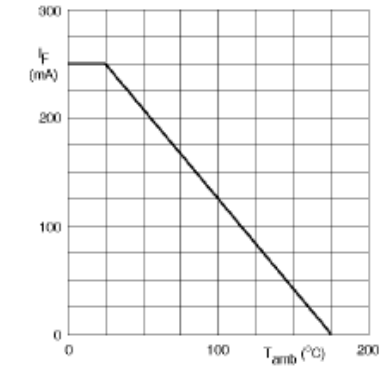
Electrical Characteristics (T_A=25℃ unless otherwise noted)

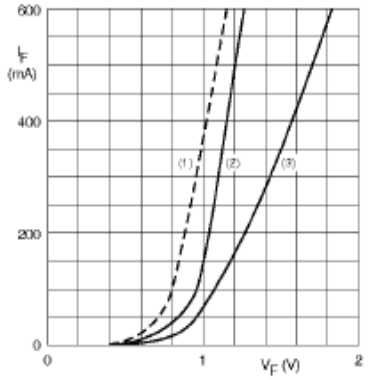
Parameter		Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA at I_F = 200 mA		V_F	 1 1.25	 V
Reverse Current at V_R = 100 V at V_R = 150 V at V_R = 200 V at V_R = 100 V, T_j = 150 ℃ at V_R = 150 V, T_j = 150 ℃ at V_R = 200 V, T_j = 150 ℃	 BAV101 BAV102 BAV103 BAV101 BAV102 BAV103	I_R	 100 100 100 100 100 100	 nA nA nA μA μA μA
Diode Capacitance at V_R = 0, f = 1 MHz		C_d	5	pF
Reverse Recovery Time at I_F = I_R = 30 mA, I_{rr} = 3 mA, R_L = 100 Ω		t_{rr}	50	ns

Ratings and Characteristic Curves



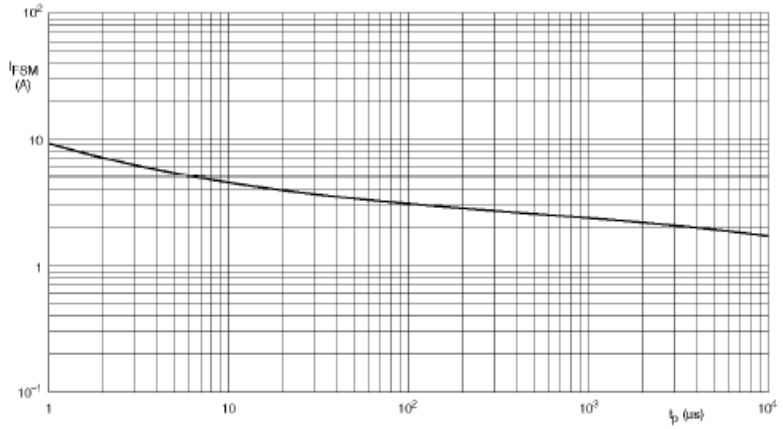
Device mounted on an FR4 printed-circuit board.

Maximum permissible continuous forward current as a function of ambient temperature.



(1) T_j = 150 °C; typical values.
(2) T_a = 25 °C; typical values.
(3) T_a = 25 °C; maximum values.

Forward current as a function of forward voltage.



Based on square wave currents.
T_a = 25 °C prior to surge.

Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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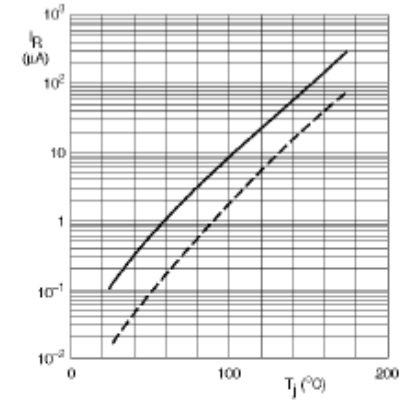
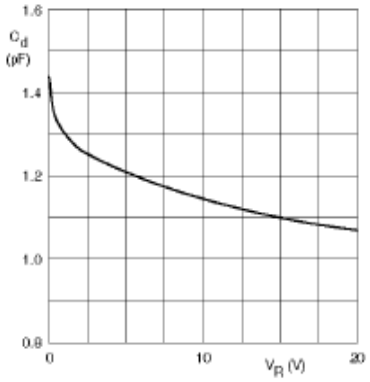
Ratings and Characteristic Curves



$V_R = V_{RRMax}$.
Solid line; maximum values.
Dotted line; typical values.

Reverse current as a function of junction temperature.



f = 1 MHz; T_j = 25 °C.

Diode capacitance as a function of reverse voltage; typical values.

Ordering Information

Part No.	Package	Packing Code	Packing
BAV101 THRU BAV103	LL-34	R25	2500pcs/Reel

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